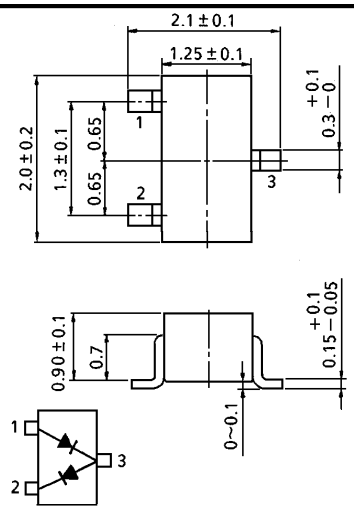
TOSHIBA DIODE SILICON EPITAXIAL PIN TYPE

1SV252

VHF~UHF BAND RF ATTENUATOR APPLICATIONS

Unit in mm



1. ANODE 2
2. CATHODE 1
3. ANODE 1 / CATHODE 2

JEDEC	—
EIAJ	SC-70
TOSHIBA	1-2P1C

Weight : 0.006 g

MAXIMUM RATINGS (Ta = 25°C)

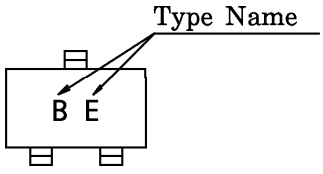
CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	I_R = 10 μA	50	—	—	V
Reverse Current	I_R	V_R = 50 V	—	—	0.1	μA
Forward Voltage	V_F	I_F = 50 mA	—	0.93	0.98	V
Total Capacitance (Note)	C_T	V_R = 50 V, f = 1 MHz	—	0.2	0.4	pF
Series Resistance	r_s	I_F = 10 mA, f = 100 MHz	—	3.5	10	Ω

(Note) : C_T is measured by 3 terminal method with capacitance bridge.

MARKING



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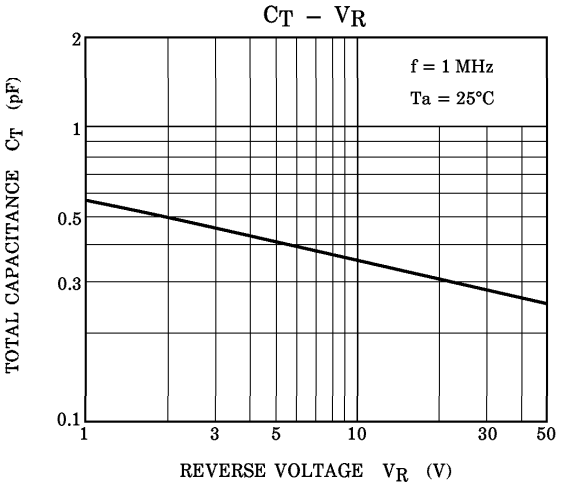
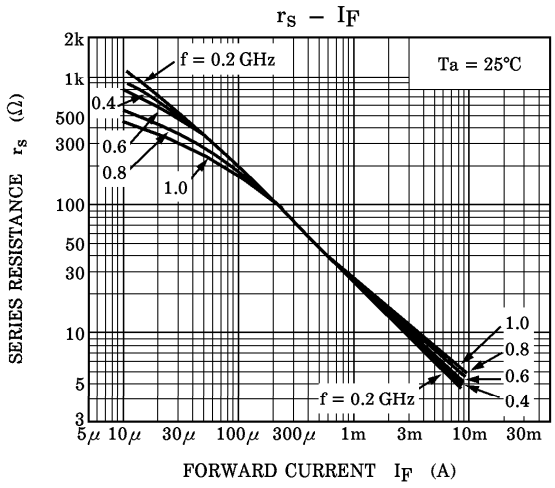

$C_T - V_R$
f = 1 MHz
Ta = 25°C
TOTAL CAPACITANCE C_T (pF)
2
1
0.5
0.3
0.1
1
3
5
10
30
50
REVERSE VOLTAGE V_R (V)


$r_S - I_F$
Ta = 25°C
f = 0.2 GHz
0.4
0.6
0.8
1.0
SERIES RESISTANCE r_S (Ω)
2k
1k
500
300
100
50
30
10
5
3
1.0
0.8
0.6
0.4
f = 0.2 GHz
5μ 10μ 30μ 100μ 300μ 1m 3m 10m 30m
FORWARD CURRENT I_F (A)